

AMENDMENTS TO THE CLAIMS

The status of the claims of the present application stands as follows:

Claim 1 (Previously canceled)

2. **(Currently amended)** An exhaust gas scrubber A system according to claim 26 27, wherein said at least one substrate is made of quartz.
3. **(Currently amended)** An exhaust gas scrubber A system according to claim 26 27, wherein said at least one substrate forms a baffle within said second chamber.
4. **(Currently amended)** An exhaust gas scrubber A system according to claim 3, wherein said baffle includes a plurality of apertures for allowing the said exhaust gas to flow through said baffle.
5. **(Currently amended)** An exhaust gas scrubber A system according to claim 26 27, further comprising a plurality of said substrates forming a series of baffles within said second chamber.
6. **(Currently amended)** An exhaust gas scrubber A system according to claim 5, wherein each baffle of said series of baffles includes a plurality of apertures for allowing the said exhaust gas to flow through each of said series of baffles.
7. **(Currently amended)** An exhaust gas scrubber A system according to claim 5, wherein said series of baffles define a serpentine passageway within said second chamber.
8. **(Currently amended)** An exhaust gas scrubber A system according to claim 26 27, further comprising a heating element for heating at least one of said second chamber and said at least one substrate.

9. (Currently amended) An exhaust gas scrubber A system according to claim 26 27, wherein said at least one substrate is removable and reusable after the film has been removed.
10. (Currently amended) An exhaust gas scrubber A system according to claim 26 27, wherein the at least one chemical said second component of the said exhaust gas is comprises silicon.

Claims 11-14 (Previously withdrawn)

15. (Currently amended) A scrubber system for scrubbing a gas containing a non-toxic part and a toxic part, the scrubber, comprising:
 - a processing chamber operatively configured to contain a process;
 - an exhaust gas generated by said process and consisting of a non-toxic part and a toxic part;
 - a first apparatus, in fluid communication with said processing chamber, and adapted for removing at least a portion of the said non-toxic part of the said exhaust gas by chemical vapor deposition; and
 - d. a second apparatus, in fluid communication with said processing chamber first apparatus, and adapted for removing at least a portion of the said toxic part from the said exhaust gas.
16. (Currently amended) A scrubber system according to claim 15, further comprising a substrate located in within said first enclosure apparatus, said substrate for receiving by chemical vapor deposition a film containing the said non-toxic part of the said exhaust gas.
17. (Currently amended) A scrubber system according to claim 15, wherein the said non-toxic part comprises silicon.
18. (Currently amended) A scrubber system according to claim 15, wherein the said toxic part comprises arsenic.

Claims 19-25 (Previously withdrawn)

26. (Canceled)

27. (New) A system, comprising:

- a. a first chamber operatively configured to contain a process;
- b. an exhaust gas resulting from said process and consisting of a first component and a second component; and
- c. a second chamber that includes an inlet and an outlet and contains at least one substrate, said inlet receiving said exhaust gas, said outlet exhausting from said second chamber substantially only said first component of said exhaust gas, and said at least one substrate having deposited thereon by vapor deposition said second component of said exhaust gas.

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